Study on the K ondo e ect in the tunneling phenom ena through a quantum dot

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A bstract

We review our recent studies on the K ondo e ect in the tunneling phenom ena through quantum dot systems. Numerical methods to calculate reliable tunneling conductance are developed. In the rst place, a case in which electrons of odd number occupy the dot is studied, and experimental results are analyzed based on the calculated result. Tunneling anom aly in the even-number-electron occupation case, which is recently observed in experiment and is ascribed to the K ondo e ect in the spin singlet-triplet cross over transition region, is also exam ined theoretically.

Key words: tunneling, quantum dot, Kondo e ect, spin crossover transition, num erical renorm alization group method

1 Introduction

Q uantum dot system s are now designed as the articial magnetic in purity and are growing as a eld of detailed experimental studies of the K ondo problem s[1]. In this report we review our recent theoretical works on the K ondo e ect in the tunneling phenomena through quantum dot [24].

A fter the papers pointed out the possibility to occur the K ondo e ect in tunneling through a quantum dot[5], m any theoretical studies have been done on this problem [6]. The calculation of the tunneling conductance needs the dynam ical excitation spectra. However we have not exact analytic calculation of the dynam ical excitation spectra for the K ondo system s[7]. Two num erical

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m ethods have been recently developed to calculate the tunneling conductance of the quantum dot system s. One is based on the num erical renorm alization group technique (NRG)[8], and another is based on the Q uantum M onte C arb (QMC) technique[3]. Both techniques are known as reliable m ethods to calculate the dynam ical excitation of the K ondo system s[7,9,10].

W hen the occupation number of electrons on the dot is odd, localized spin freedom appears on the dot, and it couples with the conduction electrons on the leads. At very low temperatures, we can expect the increase of the tunneling conductance due to the resonance transmission via the K ondo peak in the density of states on the dot orbitals. This is the most typical example of the K ondo e ect of the dot system s, and has been observed in many experiments[1]. In the rst part of this report, we present the theoretical calculation for this case[2] and compare it with experimental data [11]. Recently, anom aly in a region of an even electron number occupation case has been reported in experiment[12]. This phenomena is expected to relate to the K ondo e ect in the spin crossover region of even occupation number case[4,13,14]. This problem is discussed in the second part of this report.

2 Single Orbital Case

W e consider the following Hamiltonian,

$$H = H_{X} + H_{d} + H_{d};$$
(1)

$$H_{v} = {}^{\prime}_{k} C_{k}^{\dagger} C_{k} ;$$
 (2)

$$H_{d} = \sum_{p}^{X} u_{dp} n_{dp} + U \sum_{p \neq p^{0} > }^{X} n_{dp} n_{dp^{0}} o;$$
(3)

$$H_{v_{d}} = \frac{1}{p_{m_{p_{k}}}^{X}} fv_{p_{k}} d_{p}^{\dagger} c_{k} + hcg:$$
(4)

The term $s H \cdot and H_d$ represent the electron in the leads and the dot, respectively. The term $H \cdot_d$ gives the electron tunneling between the leads and the dot. The su x = L(R) means the left(right) lead and dp means the dot orbital denoted by p. The quantity "dp corresponds to the energy of the orbital, and it can be changed by applying gate voltage. The quantity U is the C oulom b interaction constant.

At st we consider the most simplied model that the dot has a single orbital.We abbreviate the su x p. There will be many orbitals in dot in actual situations. Two orbitals case will be discussed in x3.We calculate the conductance, G, in the linear theory of the bias voltage. It is obtained from the correlation function of the current operators [8]. But in the single orbital case, the calculation is reduced to the following expression β],

$$G = \frac{2e^2}{h} \frac{A_{L R}}{L + R} (Im G_{dd} ()) (\frac{ef}{e}) d;$$
(5)

where $G_{dd}()$ is G reen's function of the dot orbital and f() is the Ferm i distribution function.W e use this form ula in this section because the num erical calculation of $G_{dd}()$ is easier than the calculation of the current correlation function.D etailed comparison of both m ethods are m ade in R ef.[3]. Hereafter we assume that the leads have constant density of states from D to D with D = 1. The hybridization strength is parameterized as = $jy \int_{-\infty}^{2} c$, where c = 1=2D is the density of states for the lead.

In Fig.1, we show the conductance as a function of the gate voltage ("d) for various temperature cases[2]. This calculation is carried out by the NRG method. At higher temperatures we have paired C oulomb oscillation peaks at "d = U and 0. They grow without increase of their width, thus become very sharp as the temperature decreases. At the same time the peak positions shift slightly to "d = U=2 side. W hen the temperature decreases further, the intensity of the valley region between the two peaks gradually increases, and the peaks merge into a broad single peak at extrem ely low temperature. The characteristic temperature $T_{\rm KM}$ varies drastically as "d changes. (W e de ne $T_{\rm KM}$ following the usual de nition, $T_{\rm K} = 4$ (T = 0), for each "d case). It is the lowest at the mid point of the two peaks, "d = U=2, and is denoted as $T_{\rm KM}$, which is $T_{\rm KM} = 0.534$ 10 7 for the parameter case used in Fig.1. The conductance at the mid point begin to increase at about $10T_{\rm KM}$, and the valley disappears at about $0.2T_{\rm KM}$.

Goldhaber-Gordon et al. have shown the detailed tem perature dependence of the conductance[11]. We directly compare the NRG data with experimental data in Fig.2[2]. The Coulom b repulsion has been estimated to be 1.9 m eV. We have estimated = 0:12m eV = (1:3 10° m K), and thus = U = 1:9 10^{2} in the experimental situation. On horizontal axis the points "d = 0; U of the calculated conductance are set at V_g = 119; 92m eV, respectively, and factor 0.31 is multiplied to the NRG data to t the experimental data at the lowest tem perature. This factor 0.31 would be caused by the asymmetry L $\epsilon_{\rm R}$. For the left hand side peak, the conductance data agrees very well with the experimental one in 100 m K T 1500m K. This agreem ent suggests that the behaviors in experiment are caused by the K ondo e ect in the midtem perature region shown in Fig.1. The K ondo tem perature at the valley region seem s to be less than 10 m K.

There are several discrepant points. At high tem perature region T 2000 m K, the conductance of the experimental data is larger than that of the NRG



Fig. 1. Conductance as a function of "d for the parameter =(U) = 1:0 10² (U = 1:0 10²; = = 1:0 10⁴).



Fig. 2. C om parison between the experimental and the calculated data. The experimental data is reproduced from Fig2 of Ref.[11]. The parameter of the NRG calculation is chosen to be =(U) = 1:9 10²



Fig. 3. (a) Occupation numbers of the e and o orbitals at T = 0, $hn_e i$, $hn_o i$, and the total occupation number on the dot, N_d . (b) C onductance at T = 0 for the two channelcase, G_{F2} . The symbols for are common in (a) and (b). The dashed arrows show the increasing of . Parameters are $J_H = U = 0.3$, $e^{-U} = e^{-U} = 0.02$.

data. This might be caused by the multi-orbitale ect. The conductance shows disagreement in the valley and the right hand peak positions. The change of the gate voltage on the dot will a ect not only the potential of the dot, but also the hybridization strength between the dot and the lead states.

The conductance at low temperature is strongly suppressed by application of the Zeem an eld. The theoretical study has been carried out based on the QMC method β , and the result agrees well with experimental one[15].

3 Spin C rossover T ransition

Recently, Sasaki et al. observed low tem perature tunneling anom aly in evennum ber-electron-occupation case[12]. They controlled the energy splitting of orbitals by tuning the magnetic eld[16]. When the level splitting is gradually increased in the even electron number case, the energy of the spin triplet state increases compared with that of the singlet state. The electrons occupy di erent orbitals to gain H und's coupling energy in the form er state, while the electrons with opposite spin occupy the low er energy orbital in the latter state. It was suggested that the low tem perature anom aly is related to the K ondo e ect due to this spin crossover transition [13,14]. H ow ever detailed calculation of the conductance has not been done. It is observed that a bum p grow s between the two C oulom b peaks, i.e., a third peak appears between the C oulom b peaks and it grow s when the tem perature decreases. This behavior is quite di erent from that of the odd num ber case discussed in previous section.

We calculate the conductance around the singlet-triplet crossover region for a system with two orbitals[4]. The orbitals are denoted as even (p= e) and odd (p= o). The energy of e(o) orbital is de ned as $"_d = 2$ ($"_d + = 2$). The exchange term $H_{ex} = J_H_{1233}^{P}$ ()₁₂ ()₃₄ $d^+_{e_1}d_{e_2}d^+_{o_3}d_{o_4}$ is added to the Ham iltonian Eq.(1). ($J_H < 0$)



Fig. 4. Conductance at various temperatures as a function of gate voltage in the two channel case. (a) =U = 0.24, (b) =U = 0.282, (c) =U = 0.3. The symbols of the temperature in (b) and (c) are common.

In Fig.3(a), we show the occupation numbers of the even and odd orbitals, hn_ei and hn_oi , on the dot. The parameters are $J_H=\!U=0.3,\ _e=\!U=\ _o=\!U=0.02$.

We assume the case in which both leads have two conduction channels, and each dot orbital connects to each conduction channel (two channel case). The conductance is given as the sum of ones from two channels. At very low tem – peratures it is given as, $G_{F2} = (2e^2=h)^{p} \sin^2(hn_pi=2)$, and is shown in Fig.3(b).



Fig. 5. Conductance as a function of gate voltage in the single channel case. Param eters are the same to those of Fig.4 (b).

Here we de ne a quantity x = ($_{d}^{"}$)=U . In the 0 х 1 region, an electron occupies the e-orbital, $(m_e; m_o;)'$ (1;0). Next we see the 1 х 1:5 region. At = 0.24, the occupations on both orbitals are almost the same, (m_ei; m_oi) ' (1; 1), due to the strong H und's coupling. W hen increases, the 1:5 region gradually split to (2;0) where the local occupations in the 1 Х spin state is a singlet. Therefore the conductance decreases from $4e^2$ =h to 0. W e stress that the splitting is suppressed around x = 1.5 as seen in Fig.3(a). For example at = U = 0.28, the second electron tends to occupy the e-orbital when x sweeps to x = 12 from smaller x, then they redistribute to the e- and o-orbitals when x further sweeps to x = 1.5; (1;0) ! (1:6;0:3) ! (1:2;0:8). This redistribution re ects the stronger Hund's coupling near x = 1.5, at which the total occupation is close to two. The redistribution causes a bum p in the conductance around x = 1.5 at low temperatures, as seen in 0.276 =U 0284 in Fig.3(b).

In Fig.4 we show the conductance at various temperatures around the local spin singlet-triplet degeneracy. The parameters are: (a) = 0.24, (b), =U = 0.282, (c) = U = 0.3. There are the four Coulomb peaks on x = 0, 1, 2, 3 at high tem peratures. W hen the tem perature de-U=(b" (creases, the conductance in the region 0 х 1 (2 х 3), where N_d ' 1 $(N_d ' 3)$, increases to ' $2e^2 = h$, caused by the usual spin-1/2 K ondo e ect for the e-channel (o-channel). On the other hand, the region 1 х 2, where N_d ' 2, is remarkable. At (a) = U = 0.24, the conductance is large, about 4e²=h.However, the large conductance appears at extremely low temperature $(e.g., T=U = 10^{8} \text{ corresponds to } 10^{3} \text{ m K for U } 10 \text{ m eV}).W \text{ hen}$ increases

to (b) =U = 0.282, a "bump" emerges in the region 1.2 x 1.8 as the temperature decreases. For the case (c) =U = 0.3, the conductance in the region 1 x 2 is nearly constant with a sm all value. The behaviors (a)-(c) are classified into, (a) the local spin triplet K ondo e ect, (b) the singlet-triplet K ondo e ect, and (c) the usual even-odd oscillations for the dot with large energy separation [1,8].

Next we consider a case in which leads have only one conduction channel, and the both dot orbitals connect to this single channel (single channel case). In such case one orbital will hybridize mainly with even combination of L and R lead states, and another mainly with odd combination of L and R states. The tunneling via di erent orbitals interferes in this case. At T = 0, the conductance is given as $G_{F1} = (2e^2=h)\sin^2((nn_ei - nn_oi)=2)$, and is small when n_ei' n_oi . Therefore the conductance will tend to zero as T decreases to extrem e low temperature when Hund's rule coupling energy dom inates. This is contrasted to the case (a) in Fig.4.

In the singlet-triplet K ondo e ect case where the K ondo temperature is not low, the calculated temperature dependence of the conductance is not so different from that of the two channel case (Fig.4 (b)) as seen from Fig.5. This is because hn_ei and hn_oi have di erent and not-integer values as seen from Fig.3(a).

As a sum mary, we have shown that the electron occupation on orbitals redistribute to gain Hund's coupling energy in the singlet-triplet crossover region when the potential deepens. This redistribution causes a bum p, as seen in the experiment, in the conductance at low temperatures.

A cknow ledgem ents

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